

Features

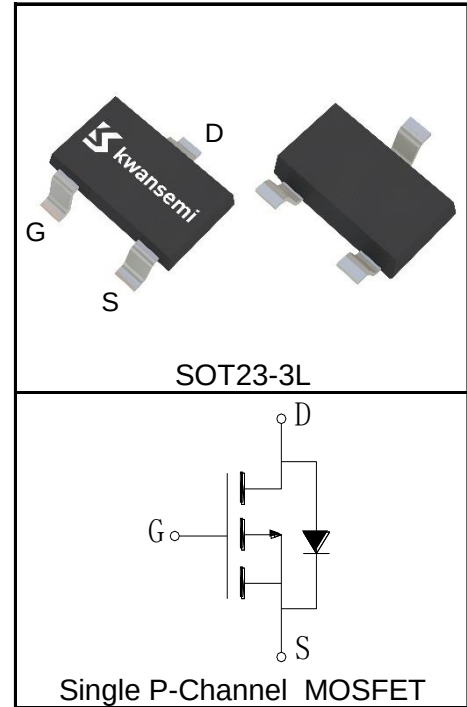
- -20V/-6.3A,
 $R_{DS(ON)} = 21m\Omega(Typ.)@V_{GS}=-4.5V$
 $R_{DS(ON)} = 27m\Omega(Typ.)@V_{GS}=-2.5V$
 $R_{DS(ON)} = 38m\Omega(Typ.)@V_{GS}=-1.8V$
- Low $R_{DS(ON)}$
- Super High Dense Cell Design
- Reliable and Rugged

Applications

- Load Switch



Pin Description



Absolute Maximum Ratings

Symbol	Parameter	Rating	Unit
Common Ratings ($T_A=25^\circ\text{C}$ Unless Otherwise Noted)			
V_{DSS}	Drain-Source Voltage	-20	V
V_{GSS}	Gate-Source Voltage	± 12	
T_{Jmax}	Maximum Junction Temperature	150	$^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to 150	$^\circ\text{C}$
I_S	Diode Continuous Forward Current	$T_A=25^\circ\text{C}$ -1.2	A
Mounted on Large Heat Sink			
$I_{DP}^{①}$	300 μs Pulse Drain Current Tested	$T_A=25^\circ\text{C}$ -25	A
$I_D^{②}$	Continuous Drain Current($V_{GS}=-4.5V$)	$T_A=25^\circ\text{C}$ -6.3	A
		$T_A=70^\circ\text{C}$ -5	
P_D	Maximum Power Dissipation	$T_A=25^\circ\text{C}$ 1.25	W
		$T_A=70^\circ\text{C}$ 0.8	
$R_{\theta JL}$	Thermal Resistance-Junction to Lead	60	$^\circ\text{C/W}$
$R_{\theta JA}^{③}$	Thermal Resistance-Junction to Ambient	100	$^\circ\text{C/W}$
Drain-Source Avalanche Ratings			
$E_{AS}^{④}$	Avalanche Energy, Single Pulsed	30	mJ

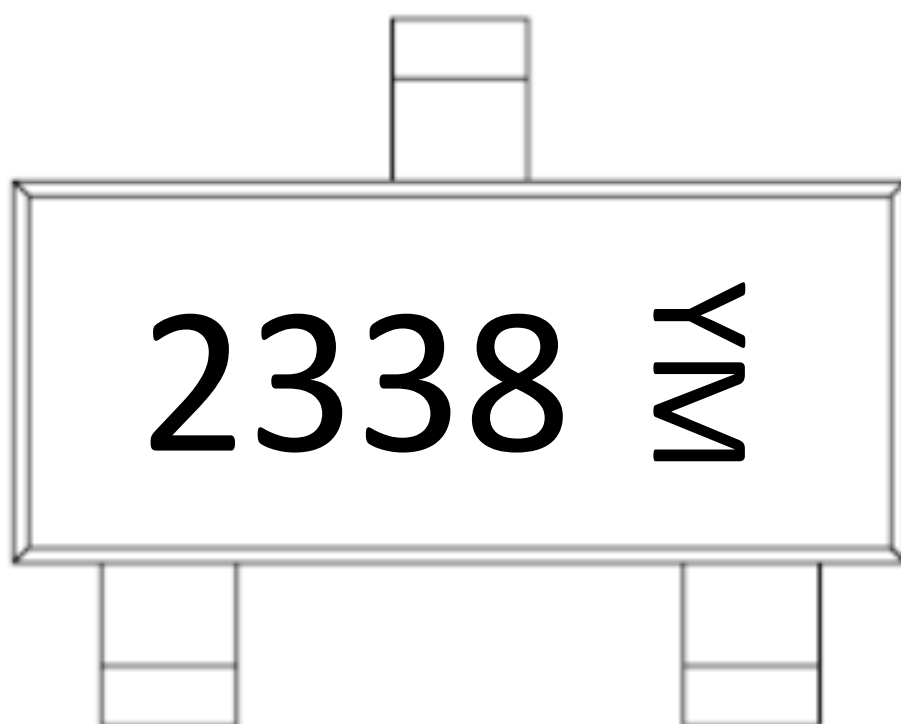
Electrical Characteristics ($T_A=25^{\circ}\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Test Condition	KS2338EA			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =-250μA	-20			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-20V, V _{GS} =0V			-1	μA
		T _J =125°C			-100	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =-250μA	-0.5	-0.7	-1	V
I _{GSS}	Gate Leakage Current	V _{GS} =±12V, V _{DS} =0V			±100	nA
R _{DS(ON)} ^⑤	Drain-Source On-state Resistance	V _{GS} =-4.5V, I _{DS} =-4A		21	24	mΩ
		V _{GS} =-2.5V, I _{DS} =-3A		27	33	mΩ
		V _{GS} =-1.8V, I _{DS} =-2A		38	60	mΩ
Diode Characteristics						
V _{SD} ^⑤	Diode Forward Voltage	I _{SD} =-4A, V _{GS} =0V		-0.84	-1.2	V
t _{rr}	Reverse Recovery Time	I _{SD} =-4A, dI _{SD} /dt=-100A/μs		8		ns
Q _{rr}	Reverse Recovery Charge			15		nC
Dynamic Characteristics ^⑥						
R _G	Gate Resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz		10		Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =-10V, Frequency=1.0MHz		1100		pF
C _{oss}	Output Capacitance			125		
C _{rss}	Reverse Transfer Capacitance			100		
t _{d(ON)}	Turn-on Delay Time	V _{DD} =-10V, I _{DS} =-4A, V _{GEN} =-4.5V, R _G =6Ω		15		ns
t _r	Turn-on Rise Time			33		
t _{d(OFF)}	Turn-off Delay Time			52		
t _f	Turn-off Fall Time			28		
Gate Charge Characteristics ^⑥						
Q _g	Total Gate Charge	V _{DS} =-10V, V _{GS} =-4.5V, I _{DS} =-4A		15		nC
Q _{gs}	Gate-Source Charge			3.1		
Q _{gd}	Gate-Drain Charge			4.2		

- Notes:
- ① Pulse width limited by safe operating area.
 - ② Calculated continuous current based on maximum allowable junction temperature.
 - ③ When mounted on 1 inch square copper board, $t \leq 10\text{sec}$. The value in any given application depends on the user's specific board design.
 - ④ Limited by T_{Jmax} , Starting $T_J = 25^{\circ}\text{C}$, $I_{ASmax} = -11A$, $L=0.5mH$, $V_{DD} = -15V$, $R_G = 25\Omega$, $V_{GS} = -4.5V$. Part not recommended for use above this value.
 - ⑤ Pulse test; Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
 - ⑥ Guaranteed by design, not subject to production testing.

Ordering and Marking Information

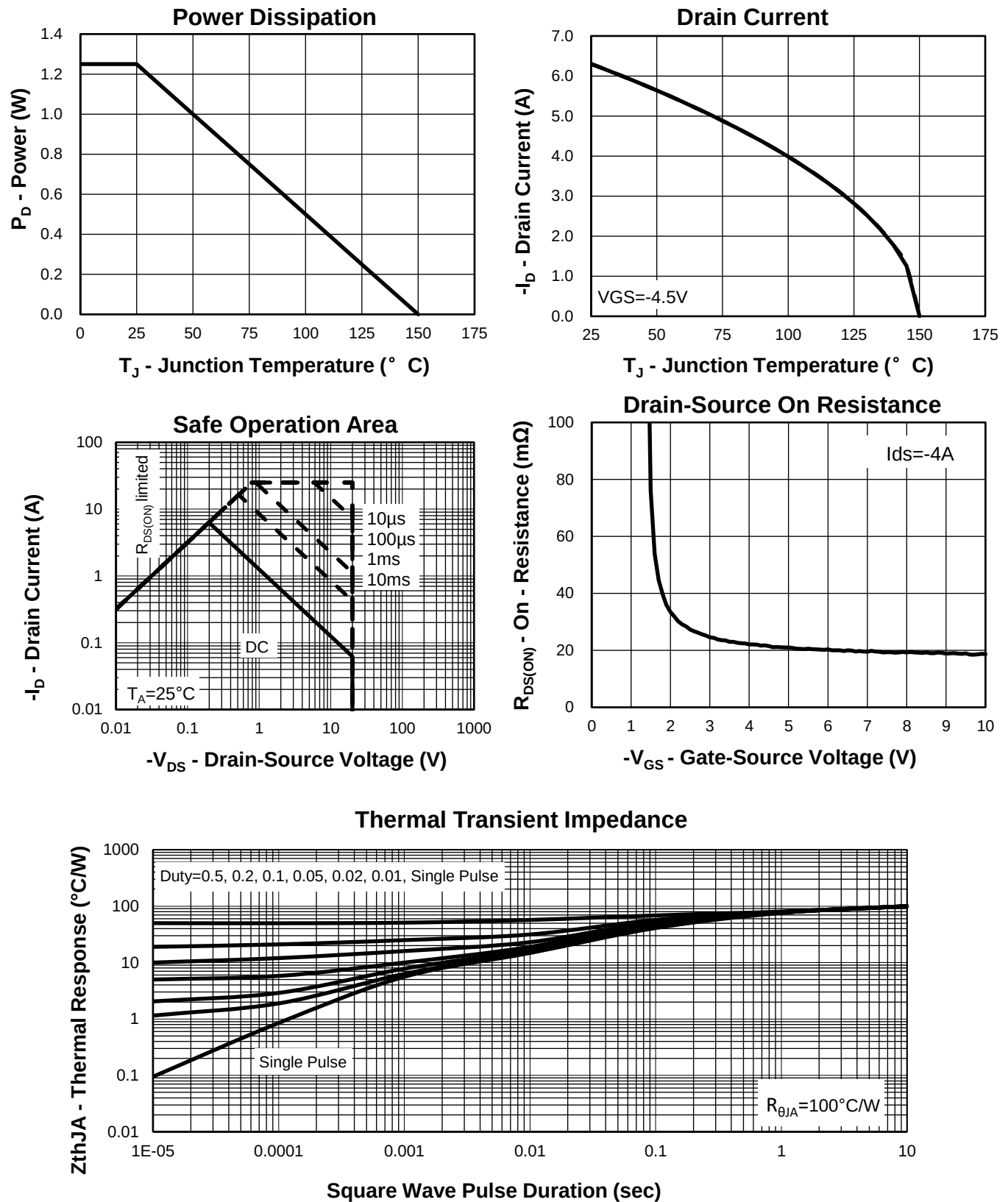
Device	Package	Packaging	Quantity	Reel Size	Tape width
KS2338EA	SOT23-3L	Tape&Reel	3000	7"	8mm



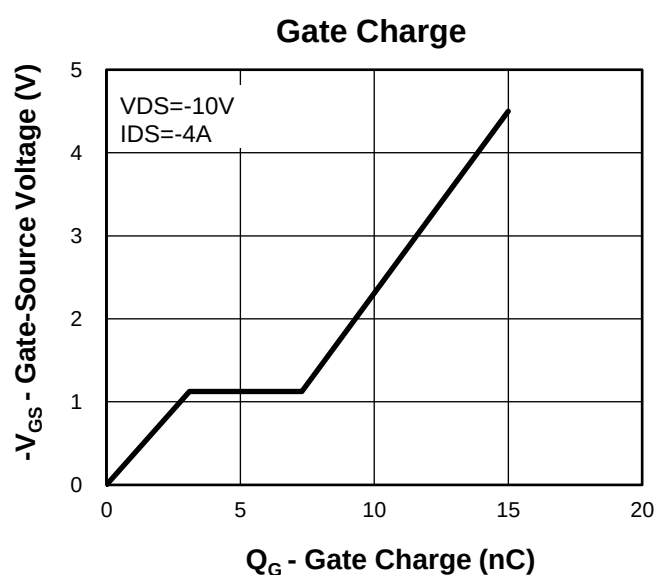
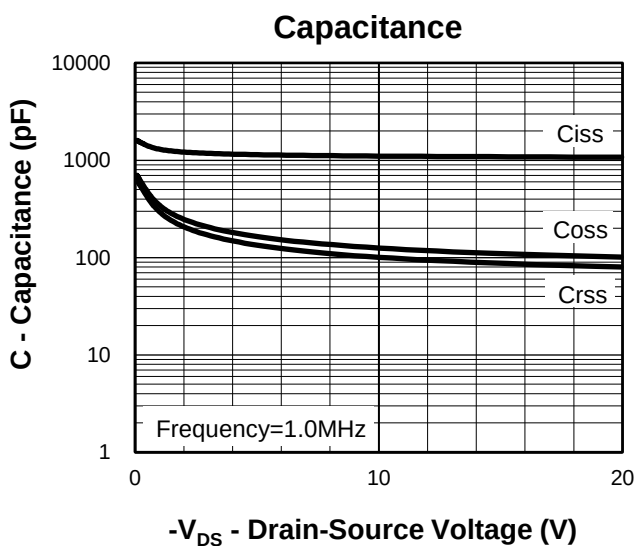
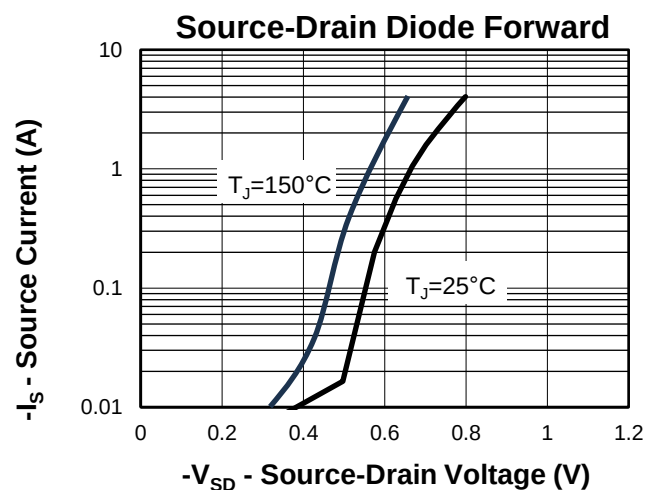
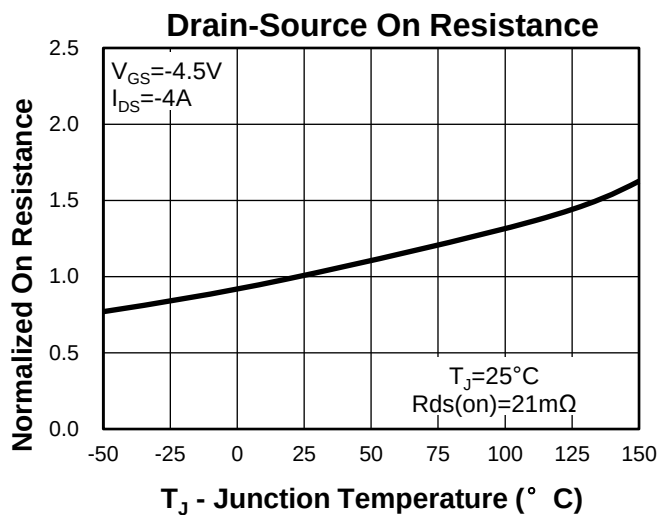
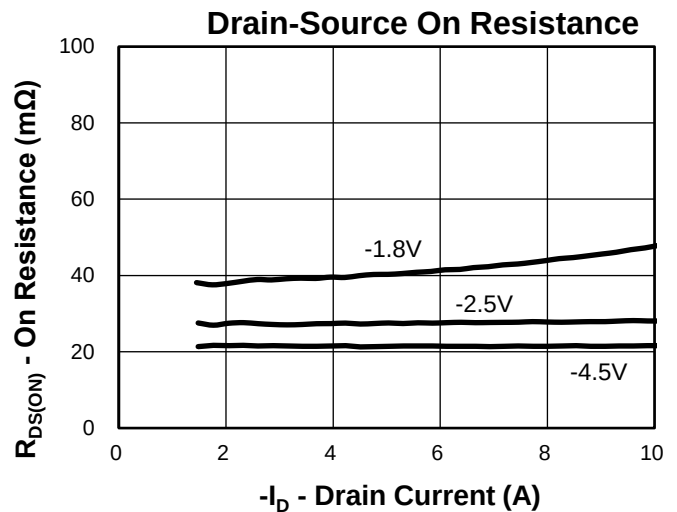
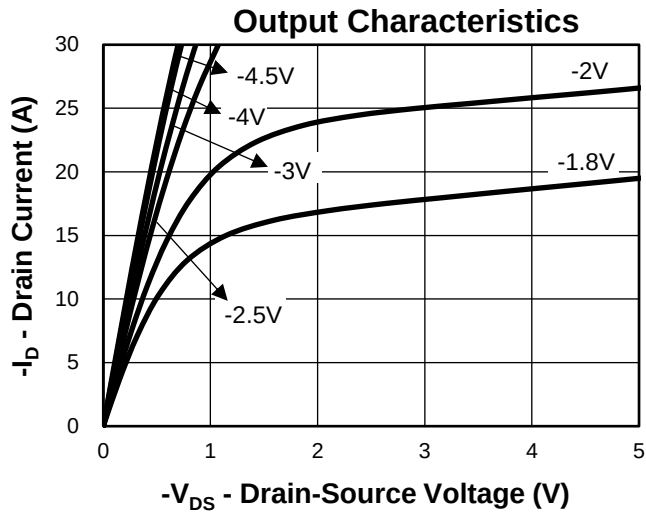
Y =Year,2017-A,2018-B,etc.

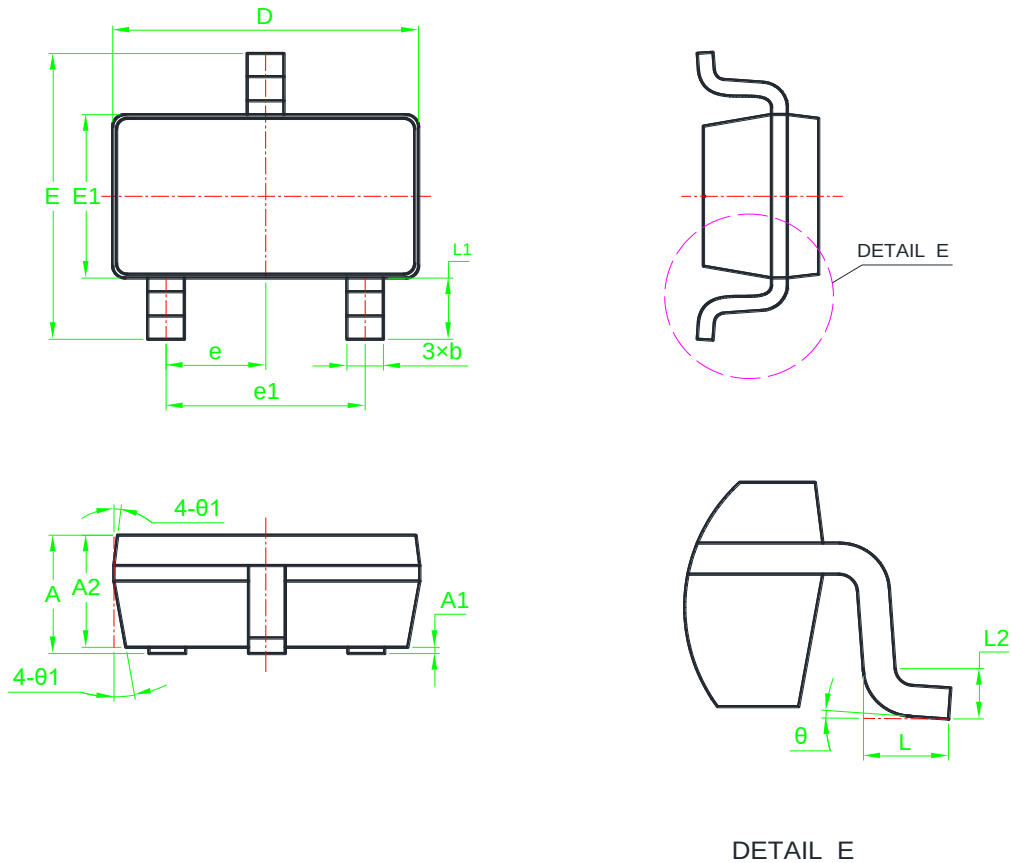
M =Month,Jan-1,Feb-2,....Sep-9,Oct-A,Nov-B,Dec-C.

Typical Characteristics



Typical Characteristics

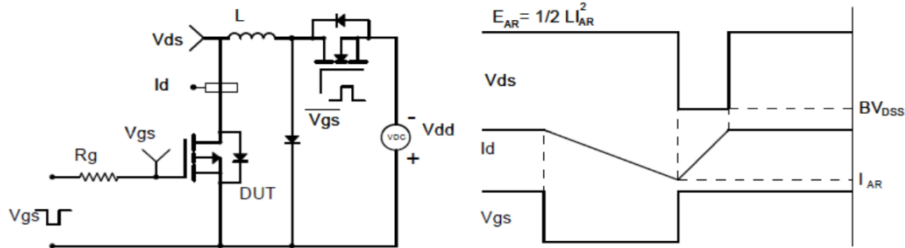


Package Information
SOT23-3L

DETAIL E

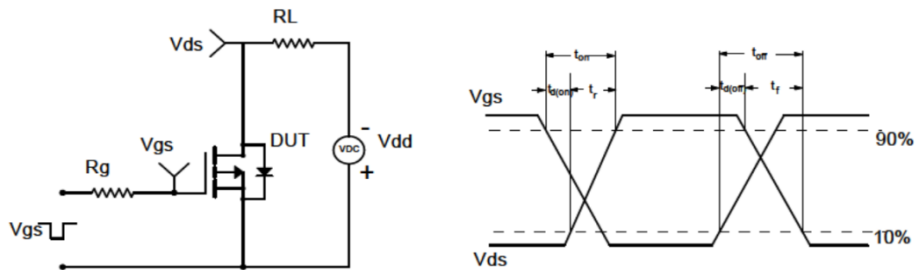
SYMBOL	MM			INCH			SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX		MIN	NOM	MAX	MIN	NOM	MAX
A	1.05	1.15	1.25	0.041	0.045	0.049	e	0.95BSC			0.037BSC		
A1	0.01	*	0.10	0.000	*	0.004	e1	1.9BSC			0.075BSC		
A2	1.05	1.10	1.15	0.041	0.043	0.045	L	0.30	0.45	0.60	0.012	0.018	0.024
b	0.30	0.40	0.50	0.012	0.016	0.020	L1	0.6REF			0.024REF		
D	2.82	2.92	3.02	0.111	0.115	0.119	L2	0.254BSC			0.01BSC		
E	2.65	2.80	2.95	0.104	0.110	0.116	θ	0°	*	8°	0°	*	8°
E1	1.50	1.60	1.70	0.059	0.063	0.067	θ 1	0°	*	10°	0°	*	10°

Note: Dimensions do not inclusive burrs and mold flash.

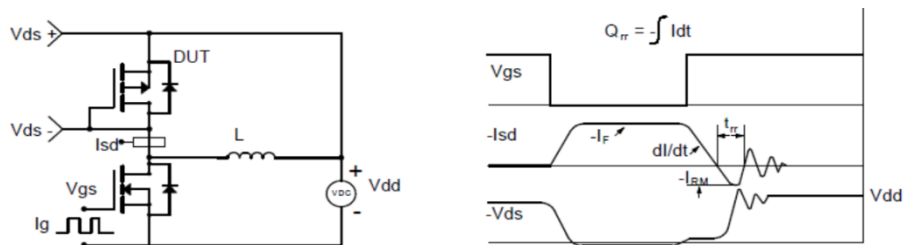
Avalanche Test Circuit and Waveforms



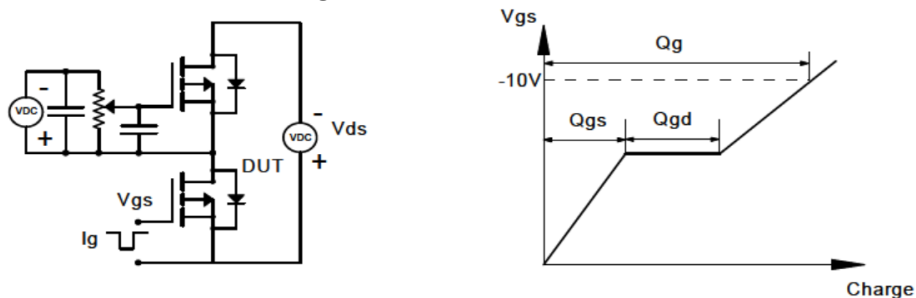
Switching Time Test Circuit and Waveforms



Diode Recovery Test Circuit and Waveforms



Gate Charge Test Circuit and Waveform



Customer Service

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